L Number	Hits	Search Text	DB	Time stamp
-	1	("20040124460").PN.	USPAT;	2004/07/08 10:28
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1130	(438/148,768,769,775,776,791,792,793,794).CCLS.	USPAT;	2004/07/08 13:43
			US-PGPUB;	
			EPO; JPO;	
		· ·	DERWENT;	
			IBM_TDB	
-	2141	(nitriding nitridation) with (poly polysilicon gate electrode)	USPAT;	2004/07/08 13:05
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	147	((438/148,768,769,775,776,791,792,793,794).CCLS.) and	USPAT;	2004/07/08 11:42
		((nitriding nitridation) with (poly polysilicon gate electrode))	US-PGPUB;	
			EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
-	832	(nitriding nitridation) with (poly polysilicon gate near	USPAT;	2004/07/08 10:39
		electrode)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	53	(((438/148,768,769,775,776,791,792,793,794).CCLS.) and	USPAT;	2004/07/08 10:39
		((nitriding nitridation) with (poly polysilicon gate electrode)))	US-PGPUB;	
		and ((nitriding nitridation) with (poly polysilicon gate near	EPO; JPO;	
		electrode))	DERWENT;	
		l	IBM_TDB	
-	264	(rtn) with (poly polysilicon gate electrode)	USPAT;	2004/07/08 11:44
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	42	(/420/440 7C0 7C0 77E 77C 704 702 702 704) CCLC \	IBM_TDB	2004/07/00 11:45
-	12	((438/148,768,769,775,776,791,792,793,794).CCLS.) and	USPAT;	2004/07/08 11:45
		((rtn) with (poly polysilicon gate electrode))	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM_TDB	
_	679	(m) with (poly polysilicon gate electrode)	USPAT;	2004/07/08 11:45
-	0/3	(11) Wild (poly polysilicon gate electrode)	US-PGPUB;	2001/07/00 11:13
			EPO; JPO;	
			DERWENT;	
]			IBM_TDB	
-	0	((438/148,768,769,775,776,791,792,793,794).CCLS.) and	USPAT;	2004/07/08 11:45
		((rn) with (poly polysilicon gate electrode))	US-PGPUB;	
		Was a series of the series of	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	80	(rpn) with (poly polysilicon gate electrode)	USPAT;	2004/07/08 11:45
		, , , , , , , , , , , , , , , , , , , ,	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	11	((438/148,768,769,775,776,791,792,793,794).CCLS.) and	USPAT;	2004/07/08 11:47
		((rpn) with (poly polysilicon gate electrode))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			_IBM_TDB	

-	1810	(oxidation oxide oxidize) near2 side near2 (gate electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/08 11:48
-	2841	(nitriding nitridation rtp rtn) with (poly polysilicon gate electrode)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/10 09:48
-	63	((oxidation oxide oxidize) near2 side near2 (gate electrode)) and ((nitriding nitridation rtp rtn) with (poly polysilicon gate electrode))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/08 11:48
-	57	(nitriding nitridation) with (poly polysilicon gate electrode) and (metal titanium tungsten molybdium nickel cobalt) near nitride same (nitrided silicion near nitride)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 13:35
-	21	("5147820" "5256455" "5279985" "5352623" "5438012" "5486488" "5508221" "5619051" "5696017" "5763315" "5801079" "5805494" "5807760" "5811336" "5854114" "5856009" "5858873" "6146959" "6171970" "6277681" "6319856").PN.	USPAT	2004/07/08 13:29
-	4436	((nitriding nitridation) with (thermal decoupled near plasma remote near plasma) dpn rpn cvd chemical near vapor near deposition ald atomic near layer near deposition) with (poly polysilicon gate electrode) with (silicon near nitride sin "si.sub.3n.sub.4" "si.sub.3 n.sub.4")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 13:40
-	12068	((nitriding nitridation) with (thermal decoupled near plasma remote near plasma) dpn rpn cvd chemical near vapor near deposition ald atomic near layer near deposition) with (poly si polysilicon silicon gate electrode) with (silicon near nitride sin "si.sub.3n.sub.4" "si.sub.3 n.sub.4") and (poly si polysilicon silicon) with (gate electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 13:41
-	9288	(pattern patterning etch\$5) with (gate electrode) with (nitride nitrided nitridation) with (silicon poly polysilicon si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/07/08 13:43
-	3068	(pattern patterning etch\$5) with (gate electrode) with (nitride nitrided nitridation) with (silicon poly polysilicon si) and (((nitriding nitridation)) with (thermal decoupled near plasma remote near plasma) dpn rpn cvd chemical near vapor near deposition ald atomic near layer near deposition) with (poly si polysilicon silicon gate electrode) with (silicon near nitride sin "si.sub.3n.sub.4" "si.sub.3 n.sub.4") and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 13:45
-	1130	(poly si polysilicon silicon) with (gate electrode)) (438/148,768,769,775,776,791,792,793,794).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 13:43

-	63	((pattern patterning etch\$5) with (gate electrode) with	USPAT;	2004/07/08 13:46
•		(nitride nitrided nitridation) with (silicon poly polysilicon si)	US-PGPUB;	
		and (((nitriding nitridation) with (thermal decoupled near	EPO; JPO;	
		plasma remote near plasma) dpn rpn cvd chemical near	DERWENT;	
		vapor near deposition ald atomic near layer near deposition)	IBM_TDB	
		with (poly si polysilicon silicon gate electrode) with (silicon		
		near nitride sin "si.sub.3n.sub.4" "si.sub.3 n.sub.4") and		
,		(poly si polysilicon silicon) with (gate electrode))) and ((438/148,768,769,775,776,791,792,793,794).CCLS.)		
<u>-</u>	665	((130/140,700,709,770,770,791,792,793,794).CCL3.) (pattern patterning etch\$5) with (gate electrode) with	USPAT;	2004/07/08 13:46
	003	(nitride nitrided nitridation) with (silicon poly polysilicon si)	US-PGPUB;	2004/07/00 13.10
		with (metal titanium tungsten molybdium nickel cobalt Ti W	EPO; JPO;	
		Mo Ni Co) and (((nitriding nitridation) with (thermal	DERWENT;	
		decoupled near plasma remote near plasma) dpn rpn cvd	IBM_TDB	
		chemical near vapor near deposition ald atomic near layer	_	
		near deposition) with (poly si polysilicon silicon gate		
		electrode) with (silicon near nitride sin "si.sub.3n.sub.4"		
		"si.sub.3 n.sub.4") and (poly si polysilicon silicon) with (gate		
		electrode))		
-	17	((pattern patterning etch\$5) with (gate electrode) with	USPAT;	2004/07/08 15:36
		(nitride nitrided nitridation) with (silicon poly polysilicon si)	US-PGPUB;	
		with (metal titanium tungsten molybdium nickel cobalt Ti W	EPO; JPO;	
		Mo Ni Co) and (((nitriding nitridation) with (thermal decoupled near plasma remote near plasma) dpn rpn cvd	DERWENT;	
		chemical near vapor near deposition ald atomic near layer	IBM_TDB	
		near deposition) with (poly si polysilicon silicon gate		
		electrode) with (silicon near nitride sin "si.sub.3n.sub.4"		
		"si.sub.3 n.sub.4") and (poly si polysilicon silicon) with (gate		
		electrode))) and		
		((438/148,768,769,775,776,791,792,793,794).CCLS.)		
-	25	surface near density near (nitrogen "n.sub.2")	USPAT;	2004/07/08 17:24
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	,	/"5710410"\ DN	IBM_TDB	2004/07/08 16:20
-	3	("5719410").PN.	USPAT; US-PGPUB;	2004/07/08 10.20
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	jp-60195975-\$.did.	USPAT;	2004/07/08 17:25
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		TO TAKACUT	IBM_TDB	2004/07/00 47 25
-	990340	ITO, TAKASHI	USPAT;	2004/07/08 17:26
		HORIE, HIROSHI	US-PGPUB;	
		SUGII, TOSHIHIRO	EPO; JPO; DERWENT;	
			IBM_TDB	•
_	990340	ITO, TAKASHI	USPAT;	2004/07/08 17:26
	3303.0	HORIE, HIROSHI	US-PGPUB;	
		SUGII, TOSHIHIRO TAKASHI-ITO	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	3132	SUGII-TOSHIHIRO TAKASHI-ITO HORIE-HIROSHI	USPAT;	2004/07/08 17:28
		ito-takashi TOSHIHIRO-SUGII	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	l		IBM_TDB_	<u> </u>

-	241	(438/\$6 257/\$6) and (SUGII-TOSHIHIRO TAKASHI-ITO HORIE-HIROSHI ito-takashi TOSHIHIRO-SUGII)	USPAT; US-PGPUB;	2004/07/10 09:47
			EPO; JPO; DERWENT;	
		4005004 UPDN	IBM_TDB	2004/07/00 47 46
-	33	4935804.URPN.	USPAT	2004/07/08 17:46
-	6	("3755026" "4117506" "4141022" "4377857" "4460980" "4558344").PN.	USPAT	2004/07/08 17:46
-	73	(decoupled near plasma near nitridation remote near plasma near nitridation) with (poly polysilicon gate electrode)	USPAT; US-PGPUB;	2004/07/10 09:48
		Treal filtridation) with (poly polysilicon gate electrode)	EPO; JPO;	
			DERWENT; IBM_TDB	
-	0	(decoupled near plasma near nitridation remote near plasma	USPAT;	2004/07/10 09:49
		near nitridation) with (poly polysilicon gate electrode) with	US-PGPUB;	, ,
		(ammonia "nh.sub.3" "n h.sub.3")	EPO; JPO;	
		,	DERWENT;	
			IBM_TDB	
-	2	(decoupled near plasma near nitridation remote near plasma	USPAT;	2004/07/10 09:53
		near nitridation) with (poly polysilicon gate electrode) same	US-PGPUB;	
		(ammonia "nh.sub.3" "n h.sub.3")	EPO; JPO;	
			DERWENT;	
			IBM_TDB	2004/27/12 22 23
-	6	(decoupled near plasma near nitridation dpn remote near	USPAT;	2004/07/10 09:56
1		plasma near nitridation rpn) with (poly polysilicon gate	US-PGPUB;	
		electrode) same (ammonia "nh.sub.3" "n h.sub.3")	EPO; JPO;	
			DERWENT;	
	4	((decoupled near plasma near nitridation dpn remote near	IBM_TDB USPAT;	2004/07/10 09:53
-		plasma near nitridation rpn) with (poly polysilicon gate	US-PGPUB;	2004/07/10 03.33
		electrode) same (ammonia "nh.sub.3" "n h.sub.3")) not	EPO; JPO;	
		((decoupled near plasma near nitridation remote near	DERWENT;	
		plasma near nitridation) with (poly polysilicon gate	IBM_TDB	
		electrode) same (ammonia "nh.sub.3" "n h.sub.3"))		
-	8	(decoupled near plasma near nitridation dpn remote near	USPAT;	2004/07/10 10:16
		plasma near nitridation rpn) with (poly polysilicon silicon si	US-PGPUB;	
		gate electrode) same (ammonia "nh.sub.3" "n h.sub.3") not	EPO; JPO;	
		((decoupled near plasma near nitridation dpn remote near	DERWENT;	
		plasma near nitridation rpn) with (poly polysilicon gate	IBM_TDB	
	_	electrode) same (ammonia "nh.sub.3" "n h.sub.3"))		
-	0	(decoupled near plasma near nitridation dpn remote near	USPAT;	2004/07/10 10:16
		plasma near nitridation rpn) with (poly polysilicon silicon si	US-PGPUB;	
		gate electrode) same (ammonia "nh.sub.3" "n h.sub.3") with ("1000") near (w watt watts)	EPO; JPO; DERWENT;	
		(1000) Heal (W Wall Walls)	IBM_TDB	
_	1	(decoupled near plasma near nitridation dpn remote near	USPAT;	2004/07/10 10:34
	_	plasma near nitridation rpn) with (poly polysilicon silicon si	US-PGPUB;	
		gate electrode) same (ammonia "nh.sub.3" "n h.sub.3")	EPO; JPO;	
		same ("1000") near (w watt watts)	DERWENT;	
			IBM_TDB	
-	0	jp-200049159-\$.did.	USPAT;	2004/07/10 10:34
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	2004/07/12 12 2
-	2	jp-2000049159-\$.did.	USPAT;	2004/07/10 10:34
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM_TDB	
L			סטו_ויוסג	